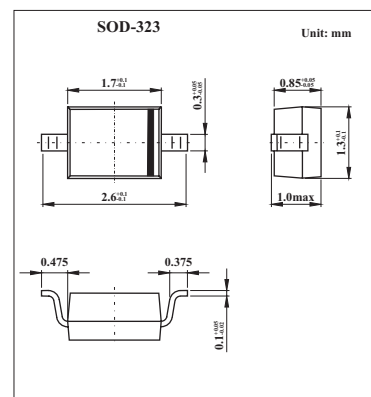


Surface Mount Fast Switching Diode

KAV16WS(BAV16WS)

■ Features

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak repetitive reverse voltage	V_{RRM}	75	V
Working peak reverse voltage	V_{RWM}		
DC blocking voltage	V_R		
RMS reverse voltage	$V_{R(RMS)}$	53	V
Average rectified output current	I_O	150	mA
Forward Continuous Current	I_{FM}	300	mA
Non-Repetitive Peak Forward Surge Current @ $t = 1.0 \mu\text{s}$	I_{FSM}	2.0	A
@ $t = 1.0\text{s}$		1.0	
Power dissipation	P_D	200	mW
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$	325	$^\circ\text{C/W}$
Operating and storage temperature range	T_j, T_{stg}	-65 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R = 1.0 \mu\text{A}$	75			V
Forward voltage	V_{FM}	$I_F = 1.0\text{mA}$ $I_F = 10\text{mA}$ $I_F = 50\text{mA}$ $I_F = 150\text{mA}$			0.745 0.855 1.0 1.25	V
Peak Reverse current	I_{RM}	$V_R = 75\text{V}$ $V_R = 75\text{V}, T_J = 150^\circ\text{C}$ $V_R = 25\text{V}, T_J = 150^\circ\text{C}$ $V_R = 20\text{V}$			1.0 50 30 25	μA μA nA nA
Junction Capacitance	C_J	$V_R = 0, f = 1.0\text{MHz}$			2.0	pF
Reverse Recovery Time	t_{rr}	$I_F = I_R = 10\text{mA}, I_{rr} = 0.1 \times I_R, R_L = 100 \Omega$			4.0	ns

■ Marking

Marking	T6 or T4
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